

C3D0606G-Silicon Carbide Schottky Diode

Z-RECTM RECTIFIER

= 600 V V_{RRM} $\mathbf{I}_{\mathsf{F}(\mathsf{AVG})} = 6 \; \mathsf{A}$

= 16 nC

Features

- 600-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

PIN 1O PIN 2O-

Package

TO-263-2

Applications

- Switch Mode Power Supplies
- **Power Factor Correction**
 - Typical PFC P_{out}: 600W-1200W
- Motor Drives
 - Typical Power : 2HP-3HP

| Part Number | Package | Marking |
|-------------|----------|----------|
| C3D06060G | TO-263-2 | C3D06060 |

Maximum Ratings

| Symbol | Parameter | Value | Unit | Test Conditions | Note |
|---|--|----------------|--------------|--|------|
| V _{RRM} | Repetitive Peak Reverse Voltage | 600 | V | | |
| V _{RSM} | Surge Peak Reverse Voltage | 600 | V | | |
| V _{DC} | DC Blocking Voltage | 600 | V | | |
| I _{F(AVG)} | Average Forward Current | 6 | А | T _c =110°C, DC | |
| I _{FRM} | Repetitive Peak Forward Surge Current | 41 27 | А | T_c =25°C, t_p = 10 ms, Half Sine Wave, D=0.3 T_c =110°C, t_p =10 ms, Half Sine Wave, D=0.3 | |
| I _{FSM} | Non-Repetitive Peak Forward Surge Current | 70 55 | А | T_c =25°C, t_p = 10 mS, Half Sine Wave, D=0.3 T_c =110°C, t_p = 10 mS, Half Sine Wave, D=0.3 | |
| I _{FSM} | Non-Repetitive Peak Forward Surge Current | 200 | А | $T_c = 25^{\circ}$ C, $t_p = 10 \mu$ s, Pulse | |
| P _{tot} | Power Dissipation | 79 34 | W | T _c =25°C T _c =125°C | |
| $T_{_{\mathtt{J}}}$, $T_{_{\mathtt{stg}}}$ | Operating Junction and Storage Temperature | -55 to +175 | °C | | |
| | TO-220 Mounting Torque | 1 8.8 | Nm lbf-in | M3 Screw 6-32 Screw | |



Electrical Characteristics

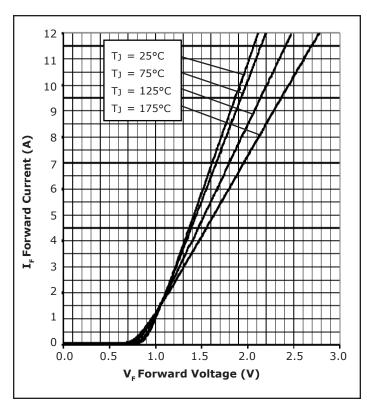
| Symbol | Parameter | Тур. | Max. | Unit | Test Conditions | Note |
|----------------|-------------------------|-----------------|------------|------|--|------|
| V _F | Forward Voltage | 1.6 1.9 | 1.8 2.4 | V | $I_F = 6 \text{ A } T_J = 25^{\circ}\text{C}$ $I_F = 6 \text{ A } T_J = 175^{\circ}\text{C}$ | |
| I _R | Reverse Current | 10 20 | 50 200 | μΑ | $V_R = 600 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 600 \text{ V } T_J = 175^{\circ}\text{C}$ | |
| Q _c | Total Capacitive Charge | 16 | | nC | $V_R = 600 \text{ V, } I_F = 6A$ $di/dt = 500 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$ | |
| С | Total Capacitance | 294 27 26 | | pF | $V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 200 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ | |

Note:

Thermal Characteristics

| Symbol | Parameter | Тур. | Unit |
|-------------------|--|------|------|
| $R_{_{	heta JC}}$ | Thermal Resistance from Junction to Case | 1.65 | °C/W |

Typical Performance





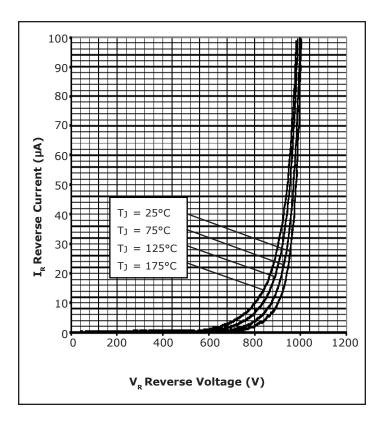
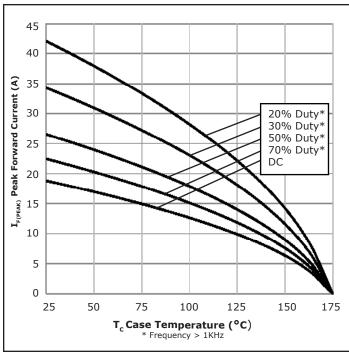


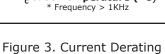
Figure 2. Reverse Characteristics

^{1.} This is a majority carrier diode, so there is no reverse recovery charge.



Typical Performance





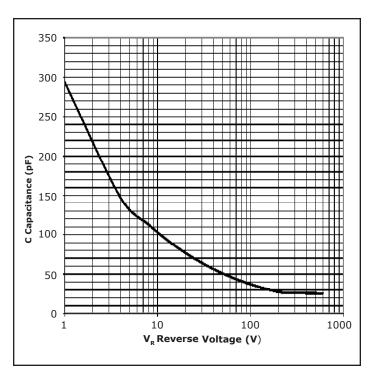


Figure 4. Capacitance vs. Reverse Voltage

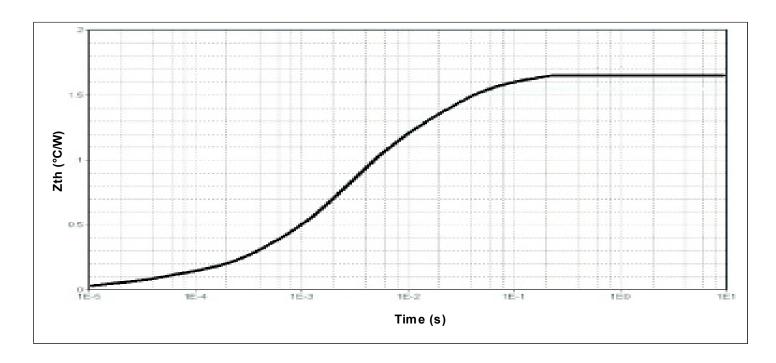


Figure 5. Transient Thermal Impedance



Typical Performance

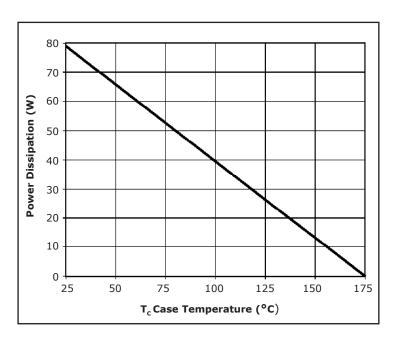
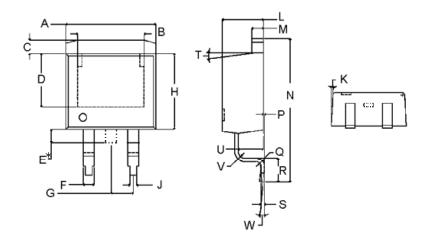


Figure 6. Power Derating



Package Dimensions

Package TO-263-2





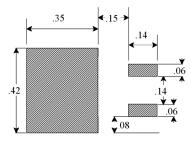
| POC | Inc | hes | Millimeters | |
|-----|---------------|---------------|---------------|---------------|
| POS | Min | Max | Min | Max |
| А | .396 | .406 | 10.058 | 10.312 |
| В | .295 | .335 | 7.493 | 8.509 |
| С | .05 | .065 | 1.27 | 1.651 |
| D | .25 | .27 | 6.35 | 6.858 |
| E* | 0.00 | .07 | 0.00 | 1.778 |
| F | .048 | .062 | 1.219 | 1.575 |
| G | .100 | TYP | 2.54 |) TYP |
| Н | .35 | .37 | 8.890 | 9.398 |
| J | .028 | .034 | .711 | .864 |
| K | 2° | 5° | 2° | 5° |
| L | .170 | .180 | 4.318 | 4.572 |
| М | .045 | .055 | 1.143 | 1.397 |
| N | .595 | .615 | 15.113 | 15.621 |
| Р | 0.00 | 0.10 | 0.00 | 2.54 |
| Q | R0.018 TYP | R0.022 TYP | R0.457 TYP | R0.559 TYP |
| R | .090 | .110 | 2.286 | 2.794 |
| S | .013 | .02 | .330 | .508 |
| Т | 6.5° | 8.5° | 6.5° | 8.5° |
| U | .100 | .107 | 2.540 | 2.718 |
| W | _ | 5.0° | _ | 5.0° |

Note:

^{*} Tab "E" may not be present



Recommended Solder Pad Layout



TO-263-2

| Part Number | Package | Marking | |
|-------------|----------|----------|--|
| C3D06060G | TO-263-2 | C3D06060 | |

Diode Model

$$V_{T}$$

$$Vf_T = V_T + If*R_T$$

$$V_{T=} 0.975 + (T_j * -1.0*10^{-3})$$

 $R_{T=} 0.09 + (T_j * 0.51*10^{-3})$

Note: T, = Diode Junction Temperature In Degrees Celcius

"The levels of environmentally sensitive, persistent biologically toxic (PBT), persistent organic pollutants (POP), or otherwise restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2002/95/EC on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April 21, 2006.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.

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